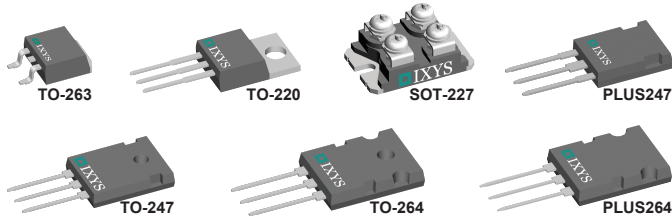


650V Ultra Junction X2-Class HiPerFET™ Power MOSFETs

Optimized for soft switching power conversion applications



FEATURES

- Low $R_{DS(on)}$ and Q_{sr}
- Fast body diode
- dv/dt ruggedness
- Avalanche rated
- Low package inductance
- International standard packages



ADVANTAGES

- Higher efficiency
- High power density
- Easy to mount
- Space savings

APPLICATIONS

- Resonant mode power supplies
- High intensity discharge (HID) lamp ballast
- AC and DC motor drives
- DC-DC converters
- Robotic and servo control
- Battery chargers
- 3-level solar inverters
- LED lighting
- Unmanned Aerial Vehicles (UAVs)



Part Number	V_{DSS} (V)	I_{D25} $T_c = 25^\circ\text{C}$ (A)	$R_{DS(on)}$ max $T_J = 25^\circ\text{C}$ (Ω)	$Q_{sl(on)}$ typ (nC)	C_{iss} typ (pF)	t_{tr} typ (ns)	$R_{th(j-c)}$ max ($^\circ\text{C}/\text{W}$)	P_D max (W)	Package Type
IXFA22N65X2	650	22	0.145	37	2190	145	0.32	390	TO-263
IXFH22N65X2	650	22	0.145	37	2190	145	0.32	390	TO-247
IXFP22N65X2	650	22	0.145	37	2190	145	0.32	390	TO-220
IXFH34N65X2	650	34	0.1	56	3230	164	0.23	540	TO-247
IXFH46N65X2	650	46	0.069	98	4570	180	0.19	660	TO-247
IXFH60N65X2	650	60	0.052	108	6300	180	0.16	780	TO-247
IXFH80N65X2	650	80	0.038	140	8300	200	0.14	890	TO-247
IXFK100N65X2	650	100	0.03	183	10800	200	0.12	1040	TO-264
IXFX100N65X2	650	100	0.03	183	10800	200	0.12	1040	PLUS247
IXFN120N65X2	650	108	0.024	240	14000	220	0.14	890	SOT-227
IXFK120N65X2	650	120	0.024	240	14000	220	0.1	1250	TO-264
IXFX120N65X2	650	120	0.024	240	14000	220	0.1	1250	PLUS247
IXFN150N65X2	650	145	0.017	355	21000	260	0.12	1040	SOT-227
IXFB150N65X2	650	150	0.017	355	21000	260	0.08	1560	PLUS264

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Efficiency Through Technology

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